



# P-Channel 30-V (D-S) MOSFET

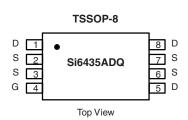
PRODUCT SUMMARY					
V <sub>DS</sub> (V)	$R_{DS(on)}(\Omega)$	I <sub>D</sub> (A)			
- 30	0.030 at $V_{GS} = -10 \text{ V}$	± 5.5			
	0.055 at V <sub>GS</sub> = - 4.5 V	± 4.1			

#### **FEATURES**

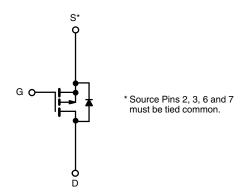
- Halogen-free
- TrenchFET® Power MOSFETs



RoHS COMPLIANT



Ordering Information: Si6435ADQ-T1-GE3 (Lead (Pb)-free and Halogen-free)



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS	A = 25 °C, unle	ss otherwise r	noted		
Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		V <sub>DS</sub>	- 30		V
Gate-Source Voltage		$V_{GS}$	± 20		
Continuous Drain Current /T 150 °C\d	T <sub>A</sub> = 25 °C	- I <sub>D</sub>	± 5.5	± 4.7	۸
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup>	T <sub>A</sub> = 70 °C		± 4.5	± 3.7	
Pulsed Drain Current (10 μs Pulse Width)		I <sub>DM</sub>	± 30		Α
Continuous Source Current (Diode Conduction) <sup>a</sup>	otion) <sup>a</sup> I <sub>S</sub> -1.35 -0.95		- 0.95		
M · D D · · · · · 3	T <sub>A</sub> = 25 °C	- P <sub>D</sub>	1.5	1.05	W
Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> = 70 °C		1.0	0.67	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150		°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Manifesture Installant to Austriant	t ≤ 10 s	- R <sub>thJA</sub>	65	83	°C/W
Maximum Junction-to-Ambient <sup>a</sup>	Steady State		100	120	
Maximum Junction-to-Foot (Drain)	Steady State	$R_{thJF}$	43	52	

#### Notes:

a. Surface Mounted on 1" x 1" FR4 board.

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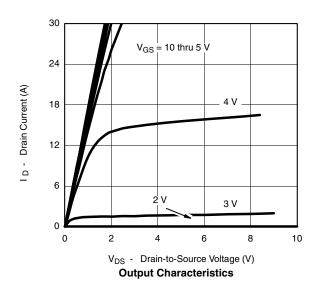
<b>SPECIFICATIONS</b> T <sub>J</sub> = 25 °C, unless otherwise noted								
Parameter	Symbol	Test Conditions Min.		Тур.	Max.	Unit		
Static								
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}$ , $I_D = -250 \mu A$	- 1.0			V		
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 100	nA		
Zero Gate Voltage Drain Current		$V_{DS} = -24 \text{ V}, V_{GS} = 0 \text{ V}$	V <sub>DS</sub> = - 24 V, V <sub>GS</sub> = 0 V					
	I <sub>DSS</sub>	V <sub>DS</sub> = - 24 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 70 °C			- 10	μΑ		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> = - 5 V, V <sub>GS</sub> = - 10 V - 30				Δ.		
		V <sub>DS</sub> = - 5 V, V <sub>GS</sub> = - 4.5 V	- 7			Α		
	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 5.5 A	0.024 0.0		0.030			
Drain-Source On-State Resistance <sup>a</sup>		$V_{GS} = -4.5 \text{ V}, I_D = -4.1 \text{ A}$		0.042	0.055	Ω		
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = - 15 V, I <sub>D</sub> = - 5.5 A		12		S		
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	I <sub>S</sub> = - 1.3 A, V <sub>GS</sub> = 0 V		- 0.8	- 1.1	V		
Dynamic <sup>b</sup>								
Total Gate Charge	$Q_g$			15	20	nC		
Gate-Source Charge	$Q_{gs}$	$V_{DS} = -15 \text{ V}, V_{GS} = -5 \text{ V}, I_{D} = -5.5 \text{ A}$		5.7				
Gate-Drain Charge	$Q_{gd}$			5.0				
Turn-On Delay Time	t <sub>d(on)</sub>			12	20			
Rise Time	t <sub>r</sub>	$V_{DD}$ = - 15 V, $R_L$ = 15 $\Omega$		10	20			
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D\cong$ - 1 A, $V_{GEN}$ = - 10 V, $R_G$ = 6 $\Omega$		42	60	ns		
Fall Time	t <sub>f</sub>			17	25			
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	$I_F = -1.3 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s}$		40	80			

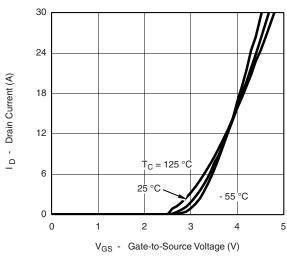
#### Notes:

- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

#### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

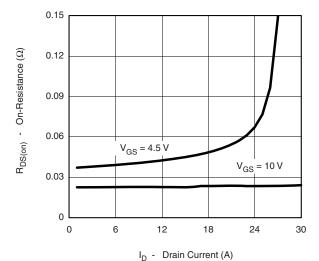




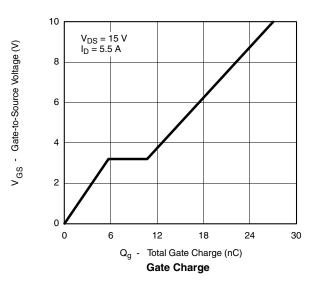
**Transfer Characteristics** 

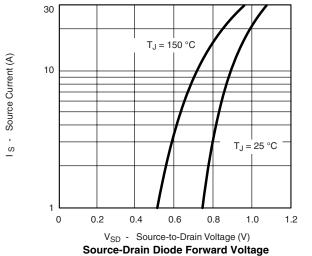


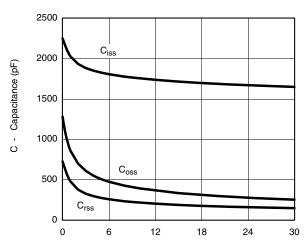
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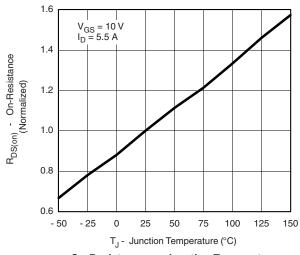
On-Resistance vs. Drain Current



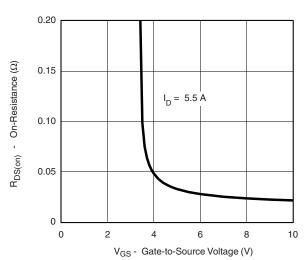




V<sub>DS</sub> - Drain-to-Source Voltage (V) **Capacitance** 



On-Resistance vs. Junction Temperature

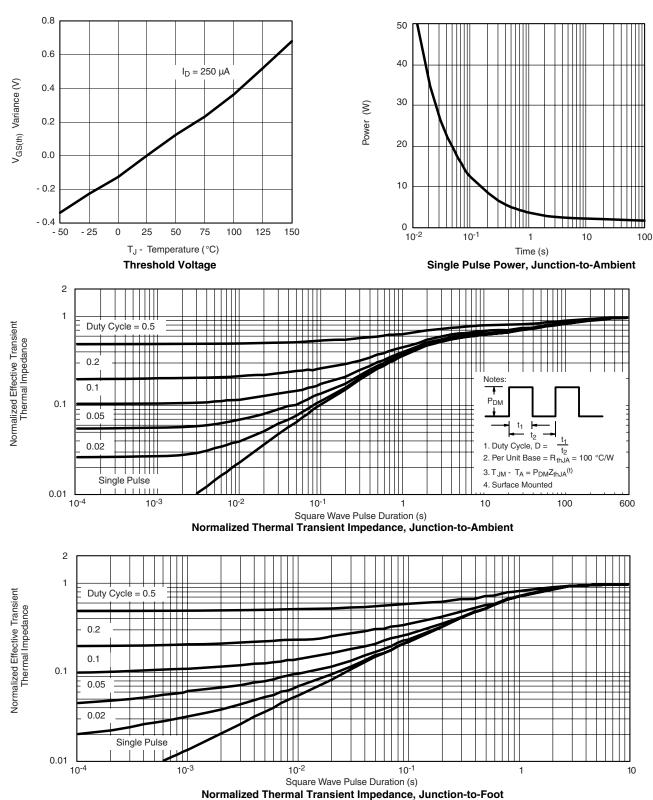


On-Resistance vs. Gate-to-Source Voltage

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### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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